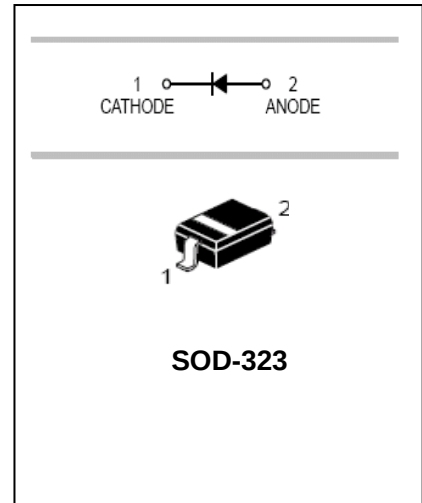


Silicon Epitaxial Planar Diode**1SS355****FEATURES**

- Small Surface Mounting Type:
SOD-323
- High Speed : $t_f=1.2\text{ns}$ Typ.
- High Reliability With High Surge Current Handling Capability.



Lead-free

**APPLICATIONS**

- High speed switching

ORDERING INFORMATION

Type No.	Marking	Package Code
1SS355	A	SOD-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Peak forward Current	I_{FM}	225	mA
Average Rectified Output Current	I_O	100	mA
Surge current (1s)	I_{surge}	500	mA
Power Dissipation	P_D	200	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{STG}	-55~+125	$^\circ\text{C}$

Silicon Epitaxial Planar Diode

1SS355

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			1.2	V	$I_F=100\text{mA}$
Reverse current	I_R			0.1	μA	$V_R=80\text{V}$
Capacitance between terminals	C_T			3	pF	$V_R=0.5\text{V}, f=1\text{MHz}$
Reverse Recovery Time	t_{rr}			4	ns	$I_F=10\text{mA}, V_R=6\text{V}, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

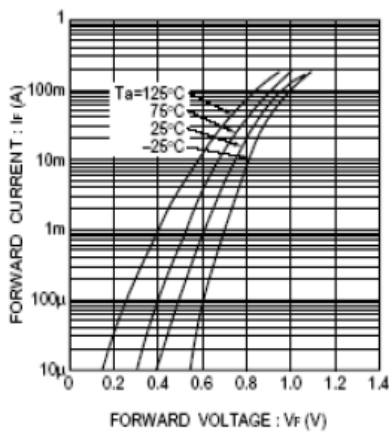


Fig.1 Forward characteristics

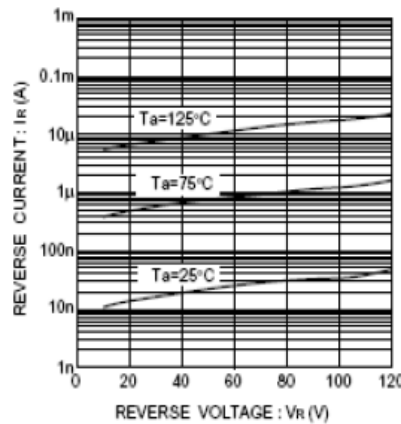


Fig.2 Reverse characteristics

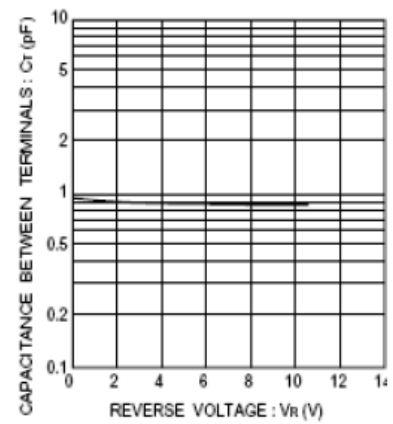


Fig.3 Capacitance between terminals characteristics

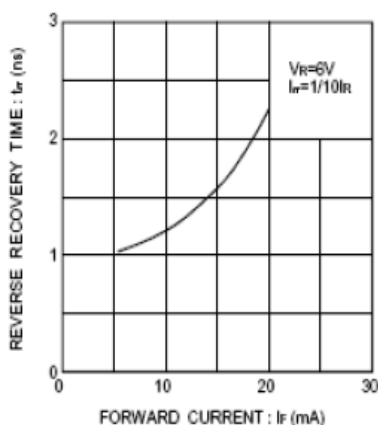


Fig.4 Reverse recovery time characteristics

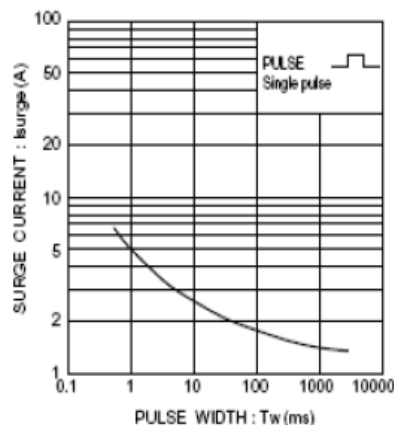


Fig.5 Surge current characteristics

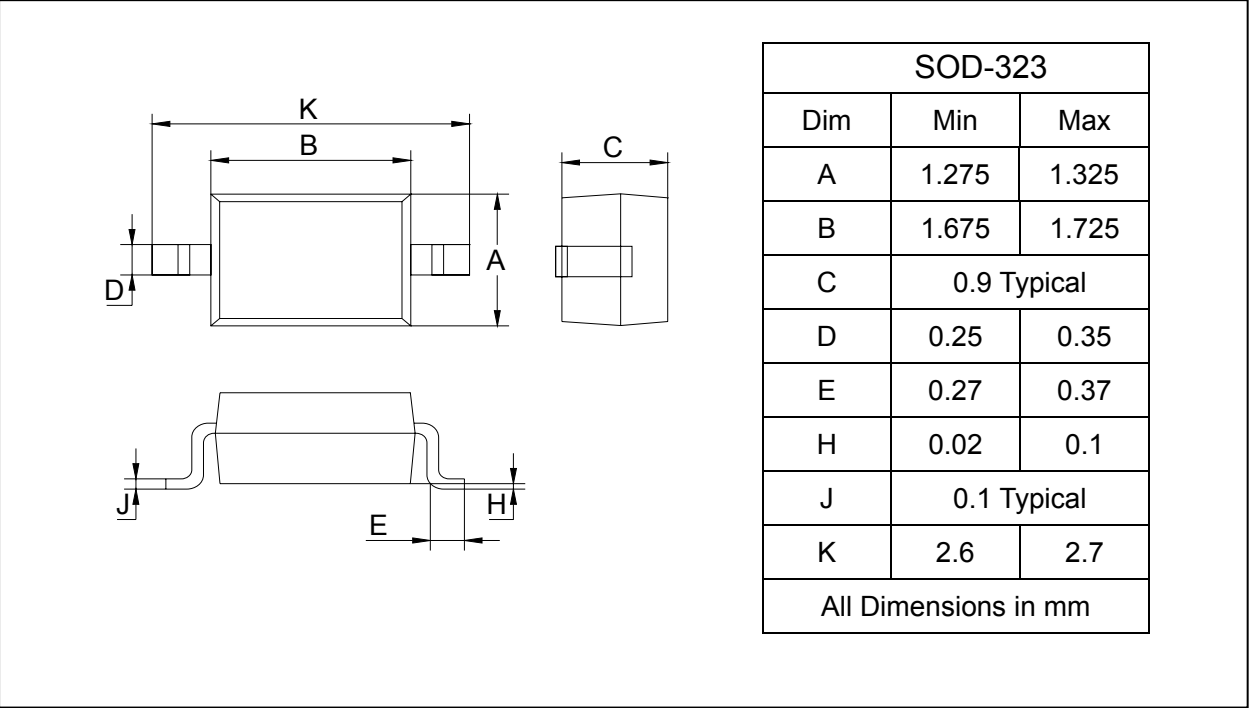
Silicon Epitaxial Planar Diode

1SS355

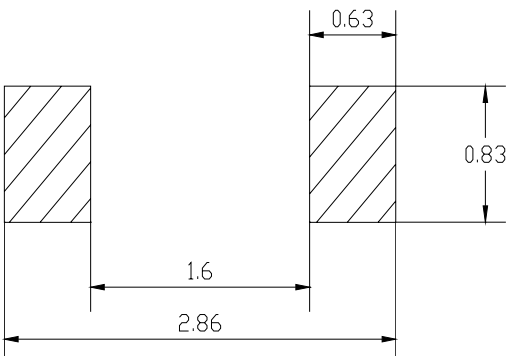
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
1SS355	SOD-323	3000/Tape&Reel